

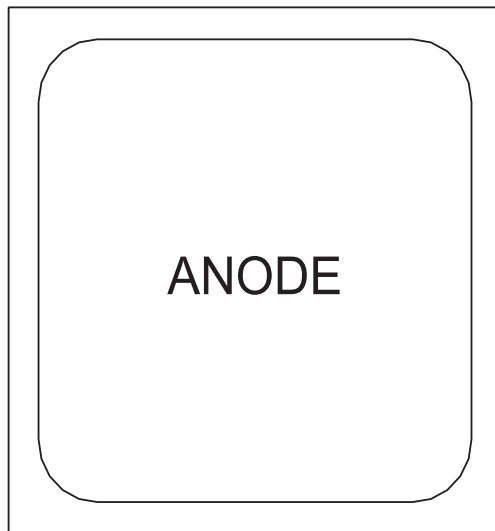
**PROCESS CPD16**  
**Ultra Fast Rectifier**  
1 Amp Glass Passivated Rectifier Chip



**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	51 x 51 MILS
Die Thickness	14 MILS
Anode Bonding Pad Area	34 x 34 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

**GEOMETRY**



BACKSIDE CATHODE

R0

**GROSS DIE PER 4 INCH WAFER**

4,250

**PRINCIPAL DEVICE TYPES**

UES1001 thru UES1003

UF4001 thru UF4007

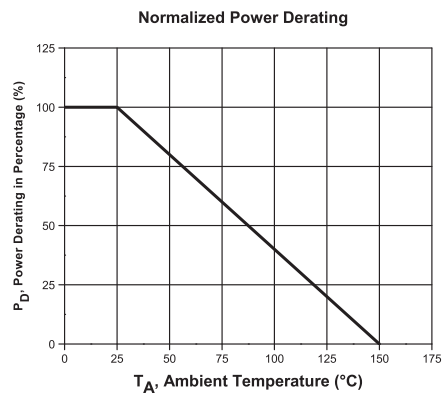
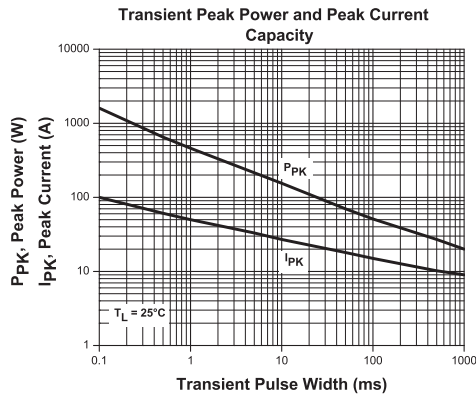
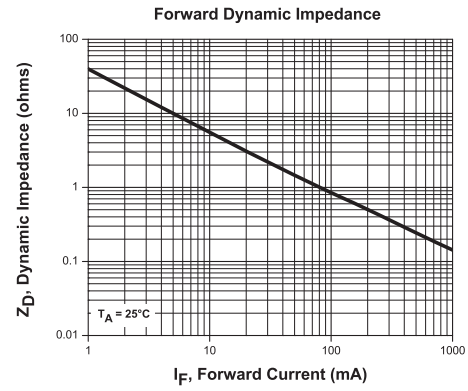
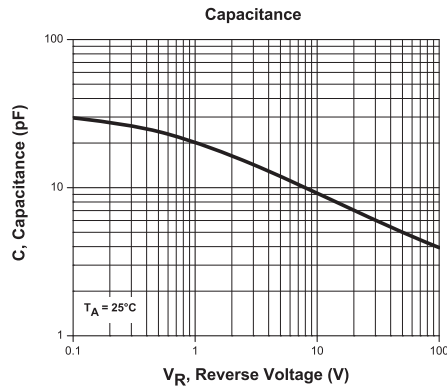
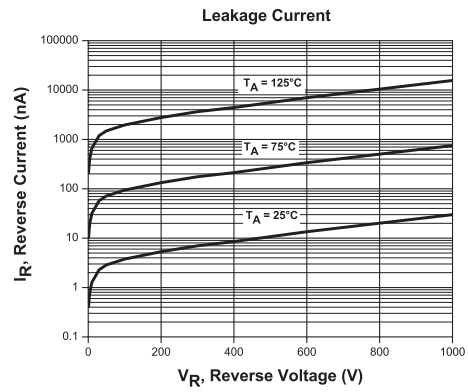
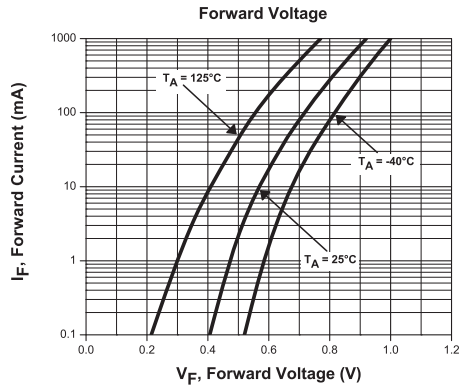
CMR1U-01 Series

CMR1U-01M Series

R4 (22-March 2010)

# PROCESS CPD16

## Typical Electrical Characteristics



R4 (22-March 2010)